

PART NUMBER

54LS126ABCA-ROCS

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All re-creations are done with the approval of the Original Component Manufacturer. (OCM)

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
 - Class Q Military
 - Class V Space Level

Qualified Suppliers List of Distributors (QSLD)

• Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OCM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

INCH-POUND MIL-M-38510/323D 14 July 2003 SUPERSEDING MIL-M-38510/323C 7 August 1987

MILITARY SPECIFICATION

MICROCIRCUITS, DIGITAL, BIPOLAR, LOW-POWER SCHOTTKY TTL, QUADRUPLE BUS BUFFER GATES WITH THREE STATE OUTPUTS, MONOLITHIC SILICON

Inactive for new design after 18 April 1997.

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 <u>Scope.</u> This specification covers the detail requirements for monolithic silicon, low-power Schottky TTL, quadruple bus buffer gates with three state outputs. Two product assurance classes and a choice of case outlines and lead finishes are provided for each type and are reflected in the complete part number. For this product, the requirements of MIL-M-38510 have been superseded by MIL-PRF-38535, (see 6.3).

1.2 Part number. The part number should be in accordance with MIL-PRF-38535, and as specified herein.

1.2.1 <u>Device types.</u> The device types should be as follows:

Device type	<u>Circuit</u>
01	Quadruple bus buffer gate (inverting control input)
02	Quadruple bus buffer gate (noninverting control input)

1.2.2 Device class. The device class should be the product assurance level as defined in MIL-PRF-38535.

1.2.3 Case outlines. The case outlines should be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
А	GDFP5-F14 or CDFP6-F14	14	Flat pack
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack
2	CQCC1-N20	20	Square leadless chip carrier

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAS, P. O. Box 3990, Columbus, OH 43216-5000, by using the self addressed Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

FSC 5962

1.3 Absolute maximum ratings.

Supply voltage range	
Storage temperature range	
Maximum power dissipation, (P _D) <u>1</u> /	
Device type 01	110 mW dc
Device type 02	121 mW dc
Lead temperature (soldering, 10 seconds)	+300°C
Thermal resistance, junction to case (θ_{JC}):	
Cases A, C, D, and 2	(See MIL-STD-1835)
Junction temperature (T _J) <u>2</u> /	+175°C

1.4 Recommended operating conditions.

Low level output current (I _{OL})	12 mA maximum
High level output current (I _{OH})	1.0 mA maximum
Supply voltage (V _{CC})	
	maximum
Minimum high level input voltage (VIH)	2.0 V dc
Maximum low level input voltage (VIL)	0.7 V dc
Case operating temperature range (T_c)	

2. APPLICABLE DOCUMENTS

2.1 Government documents.

2.1.1 <u>Specifications and Standards.</u> The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents shall be those listed in the issue of the Departments of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883	-	Test Method Standard for Microelectronics.
MIL-STD-1835	-	Interface Standard Electronic Component Case Outlines

(Unless otherwise indicated, copies of the above specifications and standards are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this specification and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

 $[\]underline{1}$ Must withstand the added P_D due to short-circuit test (e.g., I_{OS}).

^{2/} Maximum junction temperature shall not be exceeded except in accordance with allowable short duration burn-in screening condition in accordance with MIL-PRF-38535.

3. REQUIREMENTS

3.1 <u>Qualification</u>. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.4).

3.2 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.3 <u>Design, construction, and physical dimensions.</u> The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.

3.3.1 <u>Terminal connections and logic diagrams</u>. The terminal connections and logic diagrams shall be as specified on figure 1.

3.3.2 <u>Truth tables.</u> The truth tables shall be as specified on figure 2.

3.3.3 <u>Schematic circuits</u>. The schematic circuits shall be_maintained by the manufacturer and made available to the qualifying activity and the preparing activity upon request.

3.3.4 Case outlines. The case outlines shall be as specified in 1.2.3.

3.4 Lead material and finish. The lead material and finish shall be in accordance with MIL-PRF-38535 (see 6.6).

3.5 <u>Electrical performance characteristics</u>. The electrical performance characteristics are as specified in table I, and apply over the full recommended case operating temperature range, unless otherwise specified.

3.6 <u>Electrical test requirements</u>. The electrical test requirements for each device class shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table III.

3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.

3.8 <u>Microcircuit group assignment.</u> The devices covered by this specification shall be in microcircuit group number 9 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.

4.2 <u>Screening</u>. Screening shall be in accordance with MIL-PRF-38535 and shall be conducted on all devices prior to qualification and quality conformance inspection. The following additional criteria shall apply:

- a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
- c. Additional screening for space level product shall be as specified in MIL-PRF-38535.

4.3 <u>Qualification inspection</u>. Qualification inspection shall be in accordance with MIL-PRF-38535.

4.4 Technology <u>Conformance Inspection (TCI)</u>. Technology conformance inspection shall be in accordance with MIL-PRF-38535 and herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).

4.4.1 <u>Group A inspection</u>. Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:

- a. Tests shall be as specified in table II herein.
- b. Subgroups 4, 5, 6, 7, and 8 shall be omitted.
- 4.4.2 Group B inspection. Group B inspection shall be in accordance with table II of MIL-PRF-38535.

4.4.3 <u>Group C inspection</u>. Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:

- a. End-point electrical parameters shall be as specified in table II herein.
- b. Subgroups 3 and 4 shall be added to the group C inspection parameters for class B devices and shall consist of the tests, conditions, and limits specified for subgroups 10 and 11 of group A.
- c. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.4 <u>Group D inspection</u>. Group D inspection shall be in accordance with table V of MIL-PRF-38535. End-point electrical parameters shall be as specified in table II herein.

4.5 <u>Methods of inspection</u>. Methods of inspection shall be specified and as follows.

4.5.1 <u>Voltage and current.</u> All voltages given are referenced to the microcircuit ground terminal. Currents given are conventional and positive when flowing into the referenced terminal.

Test	Symbol	Conditions <u>1</u> /	Device	Limits		Unit
		$-55^{\circ}C \le T_{C} \le +125^{\circ}C$	types	Min	Max	
Input clamp voltage	V _{IC}	$V_{CC} = 4.5 \text{ V}, I_{IN} = -18 \text{ mA},$ $T_{C} = +25^{\circ}\text{C}$	01, 02		-1.5	V
High level output voltage	V _{OH}	$V_{CC} = 4.5 \text{ V}, \text{ V}_{IL} = 0.7 \text{ V},$ $V_{IH} = 2.0 \text{ V}, \text{ I}_{OH} = -1 \text{ mA}$	01, 02	2.4		V
Low level output voltage	V _{OL}	$V_{CC} = 4.5 \text{ V}, V_{IH} = 2.0 \text{ V},$ $V_{IL} = 0.7 \text{ V}, I_{OL} = 12 \text{ mA}$	01, 02		0.4	V
Off state (high impedance state) output current	I _{O(off)1}	$V_{CC} = 5.5 \text{ V}, V_{OH} = 2.4 \text{ V},$ $V_{IL} = 0.7 \text{ V}, V_{IH} = 2.0 \text{ V}$	01, 02		20	μA
Off state (high impedance state) output current	I _{O(off)2}	$V_{CC} = 5.5 \text{ V}, V_{OH} = 0.4 \text{ V}, \\ V_{IL} = 0.7 \text{ V}, V_{IH} = 2.0 \text{ V}$	01, 02		-20	μΑ
High level input current (all inputs)	I _{IH1}	$V_{CC} = 5.5 \text{ V}, V_{IH} = 2.7 \text{ V}$	01, 02		20	μΑ
High level input current (all inputs)	I _{IH2}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IH} = 5.5 \text{ V}$	01, 02		100	μΑ
Low level input current at control input	I _{IL1}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IL} = 0.4 \text{ V}$	01, 02	0	-400	μΑ
Low level input current at data input (control high) (circuit A only)	I _{IL2}	$\label{eq:Vcc} \begin{array}{l} V_{CC}=5.5 \ V, \ V_{IH}=5.5 \ V, \\ V_{IL}=0.4 \ V \end{array}$	01		-40	μA
Low level input current at data input (control low) (circuit A and B only)	I _{IL2}	$V_{CC} = 5.5 V$, Control: $V_{IL} = 0 V$ Data: $V_{IL} = 0.4 V$	02		-40	μΑ
Low level input current at data input (control low)	I _{IL3}	$V_{CC} = 5.5 V,$ Control: $V_{IL} = 0 V$ Data: $V_{IL} = 0.4 V$	01	0	-400	μA
Low level input current at data input (control high)	I _{IL3}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IH} = 5.5 \text{ V},$ $V_{IL} = 0.4 \text{ V}$	02	0	-400	μΑ
Supply current	I _{CC}	$V_{CC} = 5.5 \text{ V}, \text{ Control} = 4.5 \text{ V},$ Data = 0 V	01		20	mA
Supply current	I _{CC}	$V_{CC} = 5.5 \text{ V}, \text{ Control} = 0 \text{ V},$ Data = 0 V	02		22	mA
Short circuit output current 2/	I _{OS}	V _{CC} = 5.5 V	01, 02	-40	-225	mA

See footnotes at end of table.

Test	Symbol	Conditions <u>1</u> /	Device	Lir	nits	Unit
		$-55^{\circ}C \le T_{C} \le +125^{\circ}C$	types	Min	Max	
Propagation delay time (low to high level)	t _{PLH}	$\label{eq:CL} \begin{split} C_L &= 50 \text{ pF}, \text{ R}_L = 110 \ \Omega \\ V_{CC} &= 5.0 \text{ V} \end{split}$	01, 02	2	20	ns
Propagation delay time (high to low level)	t _{PHL}		01, 02	2	24	ns
Output enable time to high level	t _{PZH}		01	2	28	ns
			02	2	33	
Output enable time to low level	t _{PZL}		01	2	33	ns
			02	2	46	
Output disable time from	t _{PHZ}		01	2	41	ns
high level			02	2	48	
Output disable time from	t _{PLZ}		01	2	33	ns
low level			02	2	39	

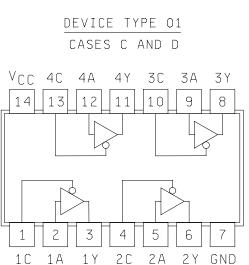
TABLE I. Electrical performance characteristics.

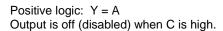
 $\underline{1}$ / Complete terminal conditions shall be as specified in table III. $\underline{2}$ / Not more than one output should be shorted at a time. The duration of any short circuit should not exceed 5 seconds.

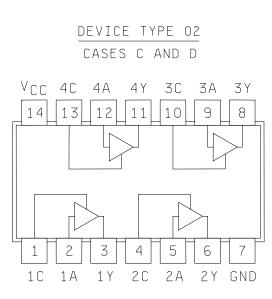
	Subgroups	(see table III)
MIL-PRF-38535	Class S	Class B
test requirements	devices	devices
Interim electrical parameters	1	1
Final electrical test parameters	1*, 2, 3, 9, 10, 11	1*, 2, 3, 9
Group A test requirements	1, 2, 3, 9, 10, 11	1, 2, 3, 9
Group B electrical test parameters when using the method 5005 QCI option	1, 2, 3, 9, 10, 11	N/A
Group C end-point electrical parameters	1, 2, 3, 9, 10, 11	1, 2, 3
Additional electrical subgroups for group C periodic inspections	N/A	10, 11
Group D end-point electrical parameters	1, 2, 3	1, 2, 3

TABLE II. Electrical test requirements.

*PDA applies to subgroup 1.







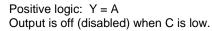


FIGURE 1. Terminal connections and logic diagram.

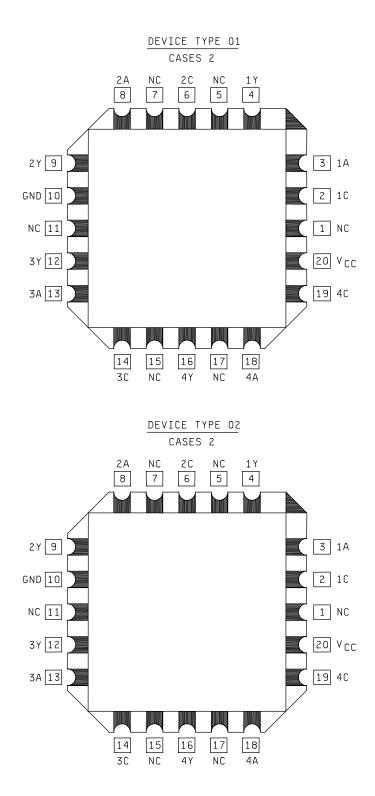


FIGURE 1. Terminal connections and logic diagram - Continued.

Device type 01

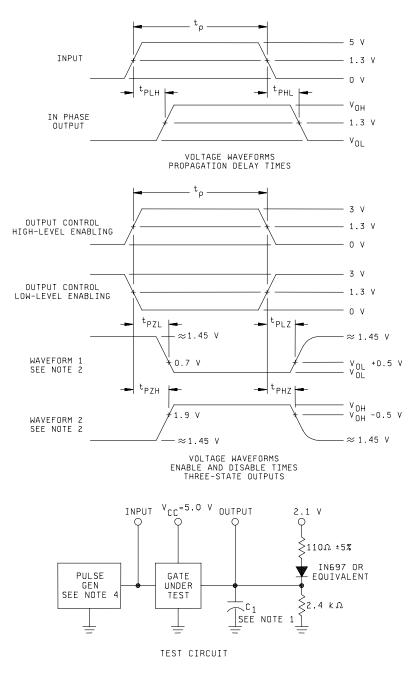
INP	UTS	
Ē	D	OUTPUT
L	L	L
L	H	Н
н	Х	Z

Device type 02

INPL	JTS	
E	D	OUTPUT
Н	L	L
Н	Н	Н
L	Х	Z

H = high level logicL = low level logicX = Doesn't matterZ = High impedance (off)

FIGURE 2. Truth tables.



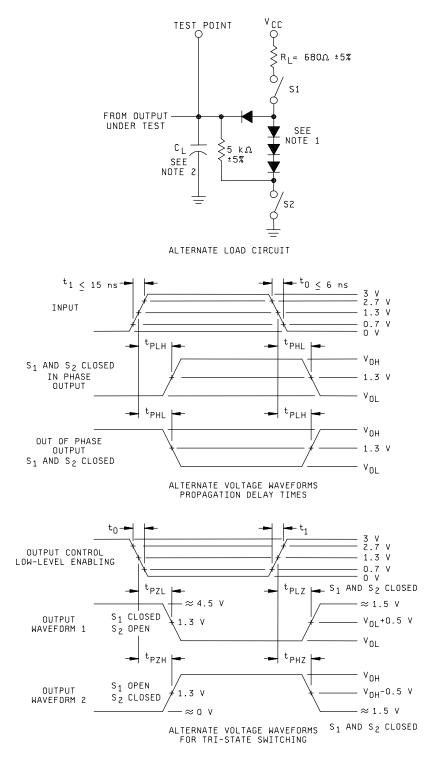
NOTES:

- 1. $C_L = 50 \text{ pF} \pm 10\%$ minimum for all tests. C_L includes scope probe and jig capacitance.
- 2. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.

Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

- 3. In the examples above, the phase relationships between inputs and outputs have been chosen arbitrarily.
- 4. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, t_p = 500 ns, Z_{OUT} \approx 50 Ω , V_{gen} = 3.0 V, t_r \leq 15 ns, t_f \leq 6 ns between 0.7 V and 2.7 V.

FIGURE 3. Switching time test circuit and waveforms.



NOTES:

- 1. Diodes are 1N3064 or equivalent.
- 2. $C_L = 50 \text{ pF} \pm 10\%$ for t_{PLH} , t_{PHL} , t_{PZL} and t_{PZH} ; $C_L = 15 \text{ pF}$ minimum for t_{PHZ} and t_{PLZ} . C_L includes probe and jig capacitance.

FIGURE 3. Switching time test circuit and waveforms - Continued.

	Ħ		Τ															T	7																									Т	Π			
	Unit	1.	>	_	-	=	-	-	-	=	-	=	-	-	-		-	-	μA	-	=		_	_	-	-		-		=	=	-	-		=		-	=	=	=	-	=	=	=	=	-	=	-
	Limits	Мах	-1.5	=	=	=	-	=	-	=					0.4	-	-	-	20	=	-	=	-20	=	-	=	20			=	=	-	-	100	=		-	=	=	=	2/	j =	=	=	-40	-	-	-
		Min									2.4	=	-	-																											٦/	<u>5</u> =	=	=				1
	Measured		1A	10	2A	2C	3A	3C	4A	4C	1Y	2Υ	3Υ	4Υ	1	2Y	3Ү	4Υ	1	2Υ	3Υ	4Υ	1	2Υ	3Υ	4Υ	5	1A 20	202	34	3C	4A	4C	1C	1A	2C	ZA	40 UC	ع م	44	4C 1C	20	30	4C	1A	2A	3A	4A
14	20	Vcr	4.5 V	=	-	=	-	-	-	-	-	-	-	-	-		-	-	5.5 V	-	-	-	-	-	-	-	-			=	-	-	-	=	-		-	-	-	=	-	-	-	-	=	-	-	-
13	19	4C	2						4.5 V	-18 mA				0.7 V				0.7 V				2.0 V				2.0 V						GND	2.7 V							GND	v c.c			0.4 V				5.5 V
12	18	4A	{						-18 mA					2.0 V (-	0.7 V (0.7 V				2.0 V						2.7 V							2 2 2	_								0.4 V
									-18						_	_	_					_		_								5.			_	+			u	ö	+		+	+				ö
11	16	47						_						-1 mA			-	12 mA				2.4 V				0.4 V														_								
10	14	30	S				4.5 V	-18 mA					0.7 V				0.7 V				2.0 V				2.0 V					GND	2.7 V							R C N	> C.C				04 \				5.5 V	L
ი	13	ЗA	5				-18 mA						2.0 V				0.7 V				0.7 V				2.0 V					0 T V	i						5 5 11	A C.C									0.4 V	
œ	12	37	5										-1 mA				12 mA				2.4 V				0.4 V																							
7	10	UN	GND	3	'n	n	-	=	3	я	3	n	-	я	3			-	u			u	μ		'n	u u	3		: 3	ä	л	n	,	n	3	3 3	. 3	3	3	3	n	3	"	n	π	n	n	3
				,								nA				٩u				۲.				>												+								+	_			
9	6	7	1		A							/ -1 mA			-	12 mA				/ 2.4 V				0.4 V				_						_		_	_				_					,		
5	ω	2A	i		-18 mA	-						2.0 V			1	0.7 V				0.7 V				2.0 V					1120	2.7						5	V C.C									0.4 V		Ļ
4	9	20	2		4.5 V	-18 mA						0.7 V				0.7 V				2.0 V				2.0 V						GIND						5.5 V	GND					041				5.5 V		
ო	4	1	-								-1 mA				12 mA				2.4 V				0.4 V																									
2	e	1A	-18 mA								2.0 V			-	0.7 V			_	0.7 V			_	2.0 V					2.7 V							5.5 V										0.4 V			. <u> </u>
			1	-							-				0.7 V 0			_					2.0 V 2					-							_	+					>	>		+				
-	2	10	~	-18 mA							0.7 V				0.7	_	_		2.0 V				2.0				2.7 V	GND						5.5 V	G						747	5		_	5.5 V			
Cases A, C, D	Cases	Test no.	-	2	З	4	5	9	7	œ	6	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	17.	02	80	31	32	33	8	35	30	50	8000	50	41	42	43	5 4	45	46	47	48
MIL-STD-	883 method										3006	=	=	-	3007		= :	=									3010			-	-	-	-	=	=		-	-	-	-	3000		-	-	=	=	-	-
	Symbol		رار ار	2							но				OL				O(off)1				O(off)2				H1							ZHI								1			112	CKT A		
	Subgroup		ſ	$Tc = 25^{\circ}C$							>				>				_				_				_							_							_				_			_

See footnotes at end of device type 01.

	Unit		Ρή	=	=		шA	=	=		-			ns	-	=	=	=	-	-	-	-	-	=	=	=	=	=	=	-	=	=	=	-	=	=	=
	Limits	Max	/ E	=	=	-	20	-225	-	- :	-			18		=	-	15	=			20	=	=	-	25	=	=	=	37	=	=	=	25	=	-	-
	Ľ	Min	/ E	=	=			-40	=		=			2		=		=						=	-	=									=	=	
	Measured terminal		1A	2A	3A	4A	V _{cc}	1Y	2Υ	3Ү	4Υ			1A to 1Y	2A to 2Y	3A to 3Y	4A to 4Y	1A to 1Y	2A to 2Y	3A to 3Y	4A to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y
14	20	V _{cc}	5.5 V	-	-			-	=	-	-			5.0 V	-	-		-		-	-	-	-	-	-	-		-	-	-		-		-	-	-	-
13	19	4C				2/	4.5 V			1	GND						GND				GND				Z				N				N				Z
12	18	4A				0.4 V	GND				4.5 V						N				Z				5.0 V				GND				5.0 V				GND
11	16	4Υ									GND						OUT				OUT				OUT				OUT				OUT				OUT
10	14	3C			2/		4.5 V			GND						GND				GND				≥				N				N				Z	
6	13	3A			0.4 V		GND			4.5 V						N				Z				5.0 V				GND				5.0 V				GND	
8	12	ЗҮ								GND		mitted.	nitted.			OUT				OUT				OUT				OUT				OUT				OUT	
7	10	GND	GND	3	-			=	и			ests are c	sts are om	GND	"	=		=	и	-	-			=	-	=				-				-	-	-	-
6	ი	2Υ							GND			and V _{IC} t	nd V _{IC} tes		OUT				OUT				OUT				OUT				OUT				OUT		
5	ω	2A		0.4 V			GND		4.5 V			= +125°C and V _{IC} tests are omitted	= -55°C a		N				N				5.0 V				GND				5.0 V				GND		
4	9	2C		2/			4.5 V		GND		-	except T _c	except $T_c = -55^{\circ}C$ and $V_{I,C}$ tests are omitted		GND				GND				N				N				N				Z		
3	4	1۲						GND				-		OUT				OUT				OUT				OUT				OUT				OUT			
2	ო	1A	0.4 V				GND	4.5 V (as for sub	as for sub	N				N				5.0 V				GND				5.0 V				GND			
-	7	1C	2/ (GND 4				nd limits a	nd limits a	GND				GND				N				U N				۲ ۷				° ⊻			
Cases A, C, D	Cases 2 <u>1</u> /	Test no.	49	50	51	52			55	56	57	conditions a	conditions a		59	60	61		63	64	65	66	67	68	69	70	71	72	73	74	75	76	77	78	79	80	81
MIL-STD-	883 method		3009	-	-	-	3005	3011	=			Same tests, terminal conditions and limits as for subgroup	Same tests, terminal conditions and limits as for subgroup 1	3003	Fig 3	=	-	=	-	=	-	=	=	=	=	=	-	=	=	=	-	=	-	=	=	-	-
	Symbol		I _{L3}				cc	so	\- -			Same test	Same test	tPHL				PLH				РZН				PZL				DHZ				PLZ			
	Subgroup		۲	Tc = 25°C								.7		6	Tc = 25°C															<u> </u>				<u> </u>			

TABLE III. Group A inspection for device type 01 - Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V, or low ≤ 0.7 V, or open).

See footnotes at end of device type 01.

	Unit	Max	24 ns	-	-	-	20 "	-	-	-		-	=	-	33 "	-	-	-	-	-	-	-	33 =	-	-	
	Limits	Min Mi	2 2	-	-	-	" 2	-		-	= 2	-	-	-	°	-	-	-	- 41		-	-	ۍ =	-	-	-
	Measured terminal		1A to 1Y	2A to 2Y	3A to 3Y	4A to 4Y	1A to 1Y	2A to 2Y	3A to 3Y	4A to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	
14	20 M	V _{cc}		=	-33	= 4	-	= 2	е -	= 4	-	" 2	е -	= 4	-	= 2	ۍ =	= 4	-	" 2	с =	= 4	-	" 2	ۍ =	-
13	19	4C	CD			GND				GND				⊒				⊻				Z				INI
12	18	4A				N				N				5.0 V				GND				5.0 V				
11	16	4Υ				OUT				OUT				OUT 5				OUT				OUT 5				
10	14	зС			GND	0			GND	0			Z	0			Z	0			z	0			z	
6	13	3A (0 N				0 N				5.0 V				GND				5.0 V				GND	
8	12	3Y			OUT				OUT				OUT 5.				OUT G				OUT 5.				OUT G	
7	10	GND	GND	n	0	=	-	3	0	=	=	=	0 =	=		=	0 -	=	-		0 =	=	=	-	0 =	=
9	9	2Y GI	ū	OUT				OUT				OUT				OUT				OUT				OUT		
2	ø	2A		⊻ Ω				N N				5.0 V				GND				5.0 V				GND		
4	9	2C		GND				GND				≧				Z				Z				Z		
3	4	1	OUT				OUT				OUT				OUT				OUT				OUT			
2	e	1A	⊒				≧				5.0 V				GND				5.0 V				GND			
1	5	10	GND				GND				≧				Z				Z				≧			
Cases A, C, D	Cases 2 1/	Test no.	82	83	84	85	98	87	88	89	06	91	92	93	94	95	96	26	86	66	100	101	102	103	104	105
MIL-STD-	883 method		3003	Fig 3	-	-	-	-	-	-	=	-	-	-	-	=	=	=	-	-	-	-	=	-	-	-
	Symbol		tPHL				нта				ΡZΗ				ΡΖΓ				ZHd				PLZ			
	Subgroup		10	Tc = 125°C							•												•			

TABLE III. Group A inspection for device type 01 - Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V, or low ≤ 0.7 V, or open).

 $\underline{1}$ Pins not referenced are NC.

 $\frac{2}{2}$ For circuits A and B, pin conditions shall be low ≤ 0.7 V; for circuits C, D, and E pin conditions shall be low ≤ 0.7 V, high ≥ 2.0 V, or open.

 $\underline{3}/$ Minimum and maximum test limits for I_{L1} and I_{L3} shall be as follows:

	ш	-140/-370	-140/-370
	D	-160/-400	0/-100
Circuits	ပ	0/-200	0/-200
	В	-120/-360	-160/-400
	A	-1.0/-150	-150/-380
	Tests	- IIL1	113

4/ Circuit E tests 54 through 57, los, min -30/max -130 mA.

Group A Inspection for device type ∪2. gnated may be high ≥ 2.0 V, or low ≤ 0.7 -150/-380, or open).	9 10	13 14 16 18 19 20 Measured Limits Unit terminal	Min Max	1A -1.5	-10 -	=	= 5C	" 3A " "	= 3C		4	2/ ==		-1 m.A 2.0 V 2.0 V " 4Y "	-	12 mA 0.7 V 2.0 V "	5.5 V	2Υ =	= = =	4Y 1Y -20	2Y		- C				2.7 V 5.5 V = 3A = = =	2.7 V 5.5 V " 4A	2.7 V " 4C	1A 00				5.5 V 5.5 V "	5.5 V "	=	= 2C =	= 3C	=		
I ABLE III. <u>Group A Inspection for devic</u> Terminal conditions (pins not designated may be high ≥ 2.0 V,		2 3 4 6 8 9 10	1C 1A 1Y 2C 2A 2Y GND	-18 mA		4.5 V -18 mA "	-18 mA		-		2011 2011 1 mA	2.0 V						0.7 V 0.7 V 2.4 V "		0.7 V 2.0 V 0.4 V	0.7 V 2.0 V 0.4 V			2.7 V 5.7 V 5.7 V 6.4 V 7.7 V	2.7V	2.7 V				5.5 V	5.5 \	> c.c		3	2		" 0.4 V	60 E			
	MIL-STD- A. C. D	Subgroup Symbol 883 Cases method 2 1/	Test no.	V _{ic}	2	m	4	ں م	9	~ ~ ~	3006	OH 2000 3	=	= 12		= 16			19		22	23	24	Н 3010 25 25 25 25 25 25 25 25 25 25 25 25 25		- 28		31			35	00	37	=	= 40		- 42	- 43	- 44	6 1	

TABLE III. Group A inspection for device type 02.

See footnotes at end of device type 01.

	Unit	1	Αų	-	-	=	тA	=	-	=	-		,	us	-	-	-	-	=	=	=	=	=	=	-	=	=		=	-	-	=	-	=	=	=
	Limits	Max	<u>/ଟ</u>	-	-	-	20	-225	-	= :	-			10	-	-	-	15	-	-	-	25	-	-	-	35	-	-	-	42	-	-	=	30	-	-
	Ē	Min	<u>)6</u>	-	=	=		-40		= :	-		¢	N	-	-	-	-	-	-	-	-	-	=	=	-	=	-	-	-	-	-	-	-	-	=
	Measured terminal		1A	2A	ЗA	4A	Vcc	1Y	2Υ	3Υ	4Υ		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	1A to 1Y	2A to 2Y	3A to 3Y	4A to 4Y	1A to 1Y	2A to 2Y	3A to 3Y	4A to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y
14	20	V _{cc}	5.5 V	-	-	-		=		= :	-			5.U V	-	-	-	-	-	=	-	=	-	=		-		-	-	-	-	=	=	-	=	-
13	19	4C				2/	GND				4.5 V						5.0 V				5.0 V				N				N				N			
12	18	4A				0.4 V	GND				4.5 V						Z				N				5.0 V				GND				5.0 V			
11	16	4γ									GND						OUT				OUT				OUT				OUT				OUT			
10	14	ЗС			2/		GND			4.5 V						5.0 V				5.0 V				N				N		ļ		N				Z
6	13	ЗA			0.4 V		GND			4.5 V						Z				N				5.0 V				GND				5.0 V				GND
8	12	ЗҮ								GND		omitted.	nitted.			OUT				OUT				OUT				OUT				OUT				OUT
7	10	GND	GND	3	=	=		=	н	= :	-	tests are	sts are or	GND	z	-	-	-	ц					=	-	=	-	"		-			=	=		=
9	ი	2Υ							GND			and V _{IC}	and V _{IC} te	!	OUT				OUT				OUT				OUT				OUT				OUT	
5	∞	2A		0.4 V			GND		4.5 V			except $I_c = +125^{\circ}C$ and V_{I_c} tests are omitted	except I _c = -55°C and V _{IC} tests are omitted		Z				N				5.0 V				GND				5.0 V				GND	
4	9	2C		2/			GND		4.5 V		H	except 1 _c	except 1 c		5.0 V				5.0 V				N				N				Z				N	
3	4	1Y						GND				bgroup 1,	bgroup 1,	INO				OUT				OUT				OUT				OUT				OUT		
2	e	1A	0.4 V				GND	4.5 V				as tor su	as tor su	z				Z				5.0 V				GND				5.0 V				GND		
-	7	10	2/				GND	4.5 V				and limits	and limits	5.U V				5.0 V				Z				Z				⊒				Z		
Cases A, C, D	Cases 2 <u>1</u> /	Test no.	49	50	51	52	53	54	55	56	57	Same tests, terminal conditions and limits as for subgroup 1	Same tests, terminal conditions and limits as for subgroup 1	58	59	60	61	62	63	64	65	66	67	68	69	70	71	72	73	74	75	76	77	78	79	80
MIL-STD-	883 method	<u> </u>	3009	=	=	=	3005	3011	=	=	=	ts, terminal	ts, terminal	3003	Fig 3	-	-	-	=	=	=	=	=	=	=	=	-	=	=	-	=	=	=	=	=	=
	Symbol		_{IL3}				cc	so	7		-	Same test	Same tes	tPHL				РСН				ΗZH				PZL				DHZ				PLZ		
	Subgroup		-	Tc = 25°C			<u> </u>	<u> </u>				N 0		ກ	Tc = 25°C							<u> </u>								<u>I</u>				<u> </u>		

TABLE III. Group A inspection for device type 02 - Continued. Terminal conditions (pins not designated may be high \geq 2.0 V, or low \leq 0.7 V, or open).

See footnotes at end of device type 01.

	Unit		su	-	-	-	-	=	-	=	-	=	-	=	=	=	=	=	-	-	=	-	=	=	=	=	
	lits	Мах	24	=	-	-	20		=		33		-		46	-	-	-	48	-		-	39	-	-	=	
	Limits	Min	2	=	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	=	-	-	-	
	Measured terminal		1A to 1Y	2A to 2Y	3A to 3Y	4A to 4Y	1A to 1Y	2A to 2Y	3A to 3Y	4A to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	1C to 1Y	2C to 2Y	3C to 3Y	4C to 4Y	
14	20	V _{cc}	5.0 V	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	=	-	-	-	=	-	-	-	
13	19	4C				5.0 V				5.0 V				N				N				N				N	
12	18	4A				Z				N				5.0 V				GND				5.0 V				GND	
11	16	4γ				OUT				OUT				OUT				OUT				OUT				OUT	
10	14	3C			5.0 V				5.0 V				Z				Z				Z				Z		
6	13	3A			Z				Z				5.0 V				GND				5.0 V				GND		
8	12	3Y			OUT				OUT				OUT				OUT				OUT				OUT		
7	10	GND	GND	n	-	-	-	"	-	-	-	-	-	-	-	-	-	-	-	-	-	-	=	-	-	=	
9	ი	2Υ		OUT				OUT				OUT				OUT				OUT				OUT			
5	ω	2A		≥				Z				5.0 V				GND				5.0 V				GND			0°75°C
4	9	2C		5.0 V				5.0 V				Z				Z				Z				Z			excent T
3	4	1	OUT				OUT				OUT				OUT				OUT				OUT				aroun 10
2	e	1A	N				N				5.0 V				GND				5.0 V				GND				as for sub
٢	5	1C	5.0 V				5.0 V				Z				Z				Z				N				and limits
Cases A, C, D	Cases 2 <u>1</u> /	Test no.	82	83	84	85	86	87	88	89	06	91	92	93	94	95	96	97	98	66	100	101	102	103	104	105	conditions a
MIL-STD-	883 method	1	3003	Fig 3	=	=	-	-	=	-	-	-	-	-	-	=	=	=	-	-	-	-	=	=	=	=	Same tests. terminal conditions and limits as for subgroup 10, except $T_c = -55^{\circ}C$.
	Symbol		tPHL				ЫЧ				ΡZΗ				PZL				DHZ				PLZ				Same tes
	Subgroup		10	Tc = 125°C			t				t				t				t				+ -				11

TABLE III. Group A inspection for device type 02 - Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V, or low ≤ 0.7 V, or open).

 $\underline{1}$ / Pins not referenced are NC.

<u>2</u>/ For circuits A and B, pin conditions shall be high ≥ 2.0 V, or open.

 $\underline{3}/$ Minimum and maximum test limits for I_{L^1} and I_{L^3} shall be as follows:

	Ш	-140/-370	-140/-370
	D	-160/-400	0/-100
Circuits	С	0/-200	0/-200
	В	-120/-360	-160/-400
	А	-150/-380	-150/-380
	Tests	الدر	Іцз

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5. PACKAGING

5.1 <u>Packaging requirements.</u> For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department of Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature which may be helpful, but is not mandatory.)

6.1 <u>Intended use.</u> Microcircuits conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

- 6.2 Acquisition requirements. Acquisition documents should specify the following:
 - a. Title, number, and date of the specification.
 - b. Complete part number (see 1.2).
 - c. Requirements for delivery of one copy of the quality conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
 - d. Requirements for certificate of compliance, if applicable.
 - e. Requirements for notification of change of product or process to contracting activity in addition to notification to the qualifying activity, if applicable.
 - f. Requirements for failure analysis (including required test condition of method 5003 of MIL-STD-883), corrective action, and reporting of results, if applicable.
 - g. Requirements for product assurance options.
 - h. Requirements for special carriers, lead lengths, or lead forming, if applicable. These requirements should not affect the part number. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
 - j. Requirements for "JAN" marking.

6.3 <u>Superseding information</u>. The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.

6.4 <u>Qualification</u>. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DSCC-VQ, 3990 E. Broad Street, Columbus, Ohio 43123-1199.

6.5 <u>Abbreviations, symbols, and definitions.</u> The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and as follows:

	Ground zero voltage potential Voltage level at an input terminal Current flowing into an input terminal
трнz	
t _{PLZ}	Output disable time from low level. The time between the specified reference points on the input and output voltage waveforms with the three state output changing from the defined low level to a high impedance (off) state.
t _{РZH}	Output enable time to high level. The time between the specified reference points on the input and output voltage waveforms with the three state output changing from a high impedance (off) state to the defined high level.
t _{PZL}	Output enable time to low level. The time between the specified reference points on the input and output voltage waveforms with the three state output changing from a high impedance (off) state to the defined low level.

6.6 Logistic support. Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired for Government logistic support will be acquired to device class B (see 1.2.2), lead material and finish A (see 3.4). Longer length leads and lead forming should not affect the part number.

6.7 <u>Substitutability.</u> The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-38510 device types and may have slight physical variations in relation to case size. The presence of this information should not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-PRF-38535.

Military device	Generic-industry
type	type
01	54LS125A
02	54LS126

6.8 <u>Manufacturers' designation</u>. Manufacturers' circuits which form a part of this specification are designated with an "X" as shown in table IV herein.

			Circuits		
Device	А	В	С	D	E
type	Texas	Signetics	National	Motorola	Fairchild
	Instruments	Corp.	Semiconductor	Inc.	Semiconductor
			Corp.		
01	Х	Х	Х	Х	Х
02	X	Х	X	X	X

TABLE IV. Manufacturers' designations.
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6.9 <u>Changes from previous issue</u>. Asterisks are not used in this revision to identify changes with respect to the previous issue due to the extensiveness of the changes.

Custodians: Army - CR Navy - EC Air Force - 11 DLA - CC Preparing activity: DLA - CC

(Project 5962-1970)

Review activities: Army - MI, SM Navy - AS, CG, MC, SH, TD Air Force - 03, 19, 99

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3. DOCUMENT TITLE MICROCIRCUITS, DIGITAL, BIPOLAR, LOW-POWER SCHOTTKY TTL, QUADRUPLE BUS BUFFER GATES WITH 3 STATE OUTPUTS, MONOLITHIC SILICON				
4. NATURE OF CHANGE (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)				
5. REASON FOR RECOMMENDATION				
6. SUBMITTER				
a. NAME (Last, First Middle Initial)	b. Of	RGANIZATION		
c. ADDRESS (Include Zip Code)	(1) C (2) D	LEPHONE (<i>Include Area Co</i> ommercial SN [;] applicable)	de) 7. DATE SUBMITTED (YYYYMMDD)	
8. PREPARING ACTIVITY				
a. NAME Defense Supply Center, Columbus		LEPHONE <i>(Include Area Co</i> ommercial 614-692-0536	de (2) DSN 850-0536	
c. ADDRESS (Include Zip Code) DSCC-VA P. O. Box 3990 Columbus, Ohio 43216-5000	Dei 872 For	IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT: Defense Standardization Program Office (DLSC-LM) 8725 John J. Kingman Road, Suite 2533 Fort Belvoir, Virginia 22060-6221 Telephone (703)767-6888 DSN 427-6888		
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